YIG-Tuned GaAs FET Oscillators

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The design and construction of a C-X straddle band YIG-tuned oscillator with 4 GHz frequency coverage is presented. A 1µ-gate GaAs FET is used for the active element, and is tuned by a YIG sphere. A one-stage single ended GaAs FET buffer amplifier is included to enhance overall performance. Power output is a minimum of 5 mW at 10 GHz, and overall performance is equal or superior to that offered by alternative swept frequency sources.

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